



PNTC114YMB

NPN resistor-equipped transistor; R1 = 10 k Ω , R2 = 47 k Ω

Rev. 1 — 16 May 2012

Product data sheet

1. Product profile

1.1 General description

NPN Resistor-Equipped Transistor (RET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package.

PNP complement: PDTA114YMB.

1.2 Features and benefits

- 100 mA output current capability
- Reduces component count
- Built-in bias resistors
- Reduces pick and place costs
- Simplifies circuit design
- AEC-Q101 qualified
- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm

1.3 Applications

- Low-current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications
- Mobile applications

1.4 Quick reference data

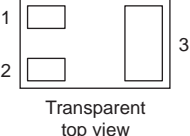
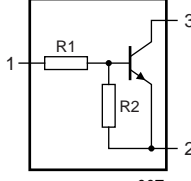
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	50	V
I _O	output current		-	-	100	mA
R1	bias resistor 1 (input)	T _{amb} = 25 °C	7	10	13	k Ω
R2/R1	bias resistor ratio		3.7	4.7	5.7	



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	I	input (base)	 Transparent top view SOT883B (DFN1006B-3)	 sym007
2	G	GND (emitter)		
3	O	output (collector)		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PDTC114YMB	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B

4. Marking

Table 4. Marking codes

Type number	Marking code
PDTC114YMB	0011 0000

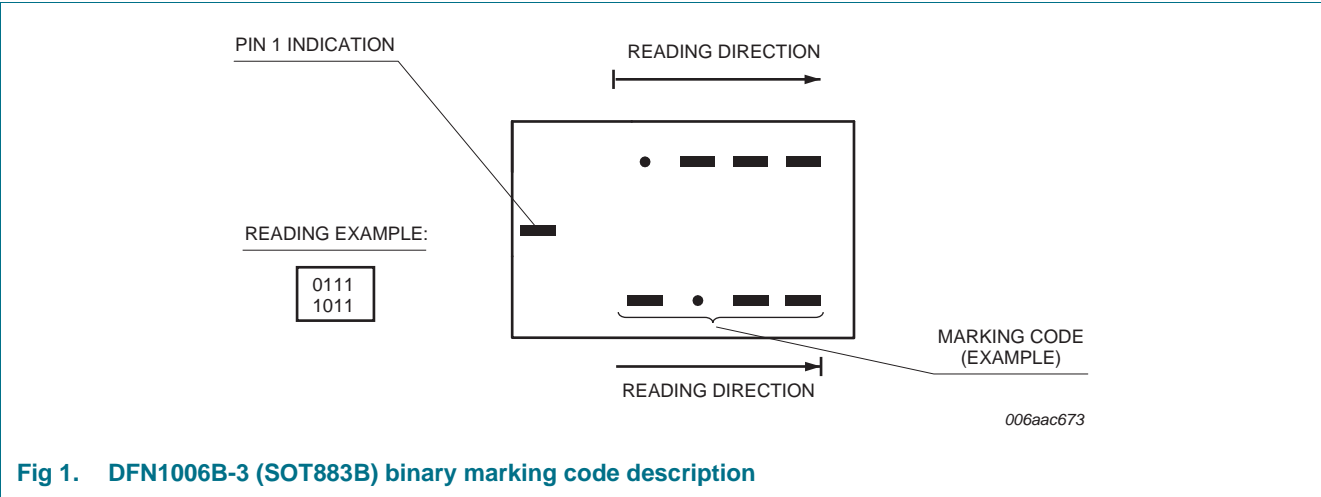


Fig 1. DFN1006B-3 (SOT883B) binary marking code description

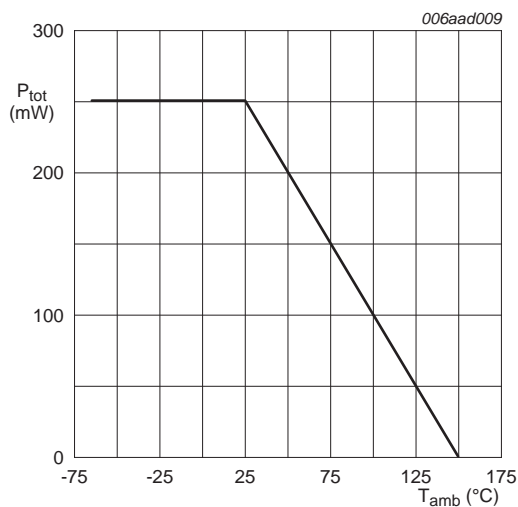
5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	50	V
V_{CEO}	collector-emitter voltage	open base	-	50	V
V_{EBO}	emitter-base voltage	open collector	-	6	V
V_I	input voltage	positive	-	40	V
		negative	-	-6	V
I_O	output current		-	100	mA
I_{CM}	peak collector current	pulsed; $t_p \leq 1$ ms	-	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C [1]	-	250	mW
T_j	junction temperature		-	150	°C
T_{amb}	ambient temperature		-65	150	°C
T_{stg}	storage temperature		-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



FR4 PCB, standard footprint

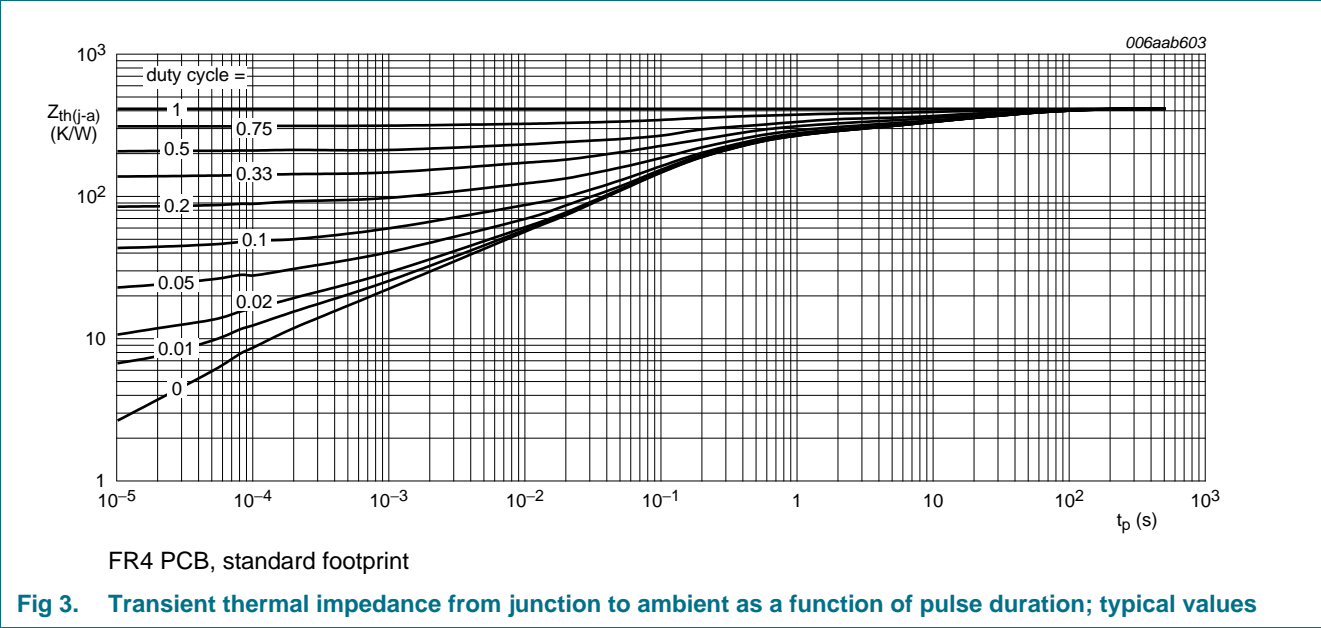
Fig 2. Power derating curve for DFN1006B-3 (SOT883B)

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	-	500	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

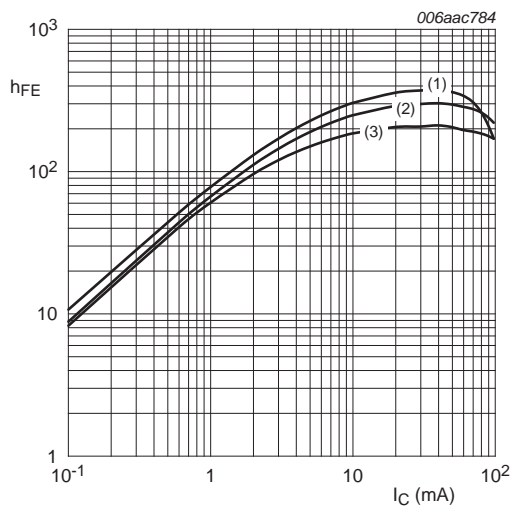


7. Characteristics

Table 7. Characteristics

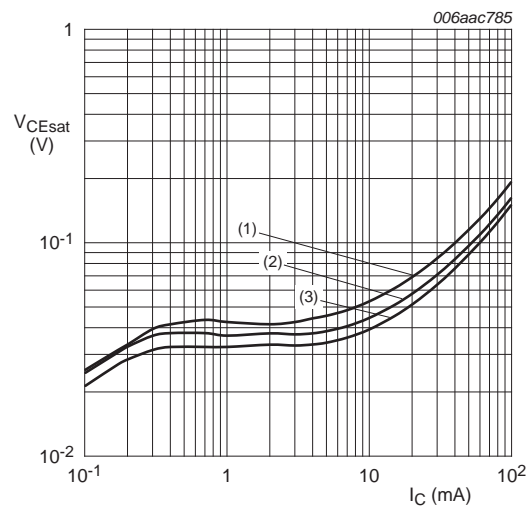
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	$V_{CB} = 50\text{ V}$; $I_E = 0\text{ A}$; $T_{amb} = 25\text{ °C}$	-	-	100	nA
I_{CEO}	collector-emitter cut-off current	$V_{CE} = 30\text{ V}$; $I_B = 0\text{ A}$; $T_{amb} = 25\text{ °C}$	-	-	1	μA
		$V_{CE} = 30\text{ V}$; $I_B = 0\text{ A}$; $T_j = 150\text{ °C}$	-	-	5	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5\text{ V}$; $I_C = 0\text{ A}$; $T_{amb} = 25\text{ °C}$	-	-	150	μA
h_{FE}	DC current gain	$V_{CE} = 5\text{ V}$; $I_C = 5\text{ mA}$; $T_{amb} = 25\text{ °C}$	100	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 5\text{ mA}$; $I_B = 0.25\text{ mA}$; $T_{amb} = 25\text{ °C}$	-	-	100	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5\text{ V}$; $I_C = 100\text{ μA}$; $T_{amb} = 25\text{ °C}$	-	0.7	0.5	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3\text{ V}$; $I_C = 1\text{ mA}$; $T_{amb} = 25\text{ °C}$	1.4	0.8	-	V
R1	bias resistor 1 (input)	$T_{amb} = 25\text{ °C}$	7	10	13	kΩ
R2/R1	bias resistor ratio		3.7	4.7	5.7	
C_C	collector capacitance	$V_{CB} = 10\text{ V}$; $I_E = 0\text{ A}$; $i_e = 0\text{ A}$; $f = 1\text{ MHz}$; $T_{amb} = 25\text{ °C}$	-	-	2.5	pF
f_T	transition frequency	$V_{CE} = 5\text{ V}$; $I_C = 10\text{ mA}$; $f = 100\text{ MHz}$; $T_{amb} = 25\text{ °C}$	[1]	230	-	MHz

[1] Characteristics of built-in transistor.



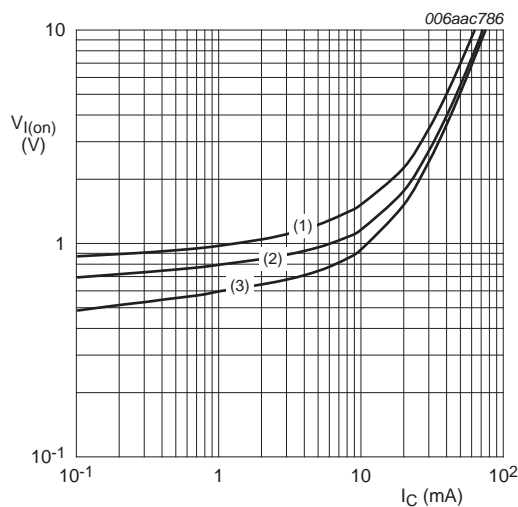
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -40\text{ °C}$

Fig 4. DC current gain as a function of collector current; typical values



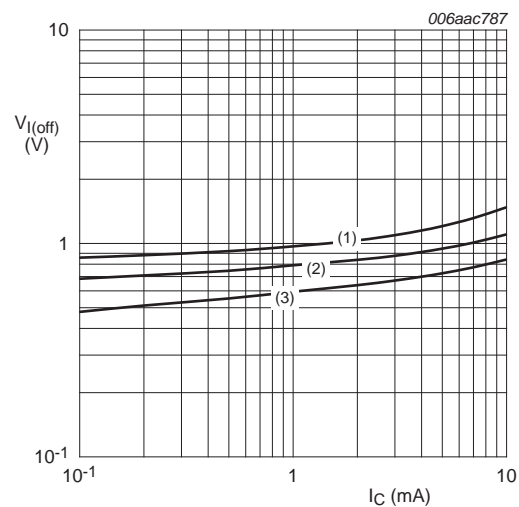
$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -40\text{ °C}$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values



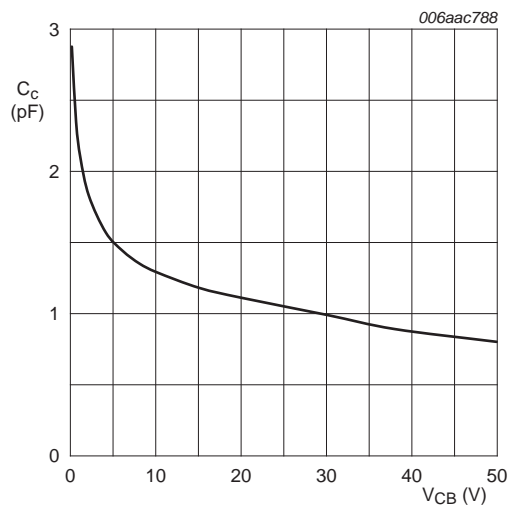
$V_{CE} = 0.3\text{ V}$
(1) $T_{amb} = -40\text{ }^{\circ}\text{C}$
(2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
(3) $T_{amb} = 100\text{ }^{\circ}\text{C}$

Fig 6. On-state input voltage as a function of collector current; typical values



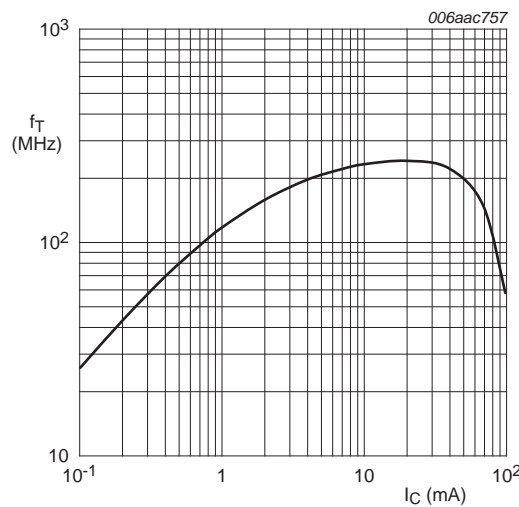
$V_{CE} = 5\text{ V}$
(1) $T_{amb} = -40\text{ }^{\circ}\text{C}$
(2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
(3) $T_{amb} = 100\text{ }^{\circ}\text{C}$

Fig 7. Off-state input voltage as a function of collector current; typical values



$f = 1\text{ MHz}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$

Fig 8. Collector capacitance as a function of collector-base voltage; typical values



$V_{CE} = 5\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$

Fig 9. Transition frequency as a function of collector current; typical values of built-in transistor

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

9. Package outline

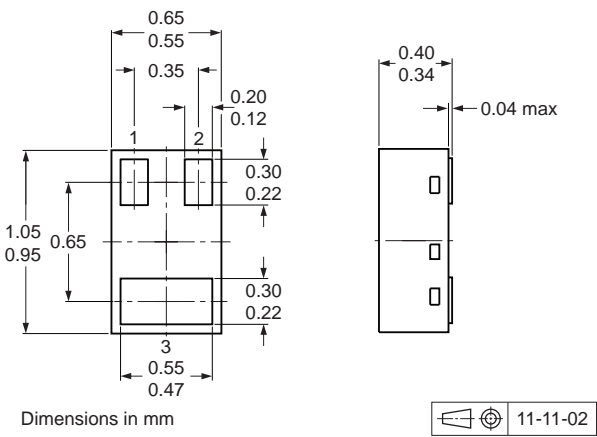


Fig 10. Package outline SOT883B (DFN1006B-3)

10. Soldering

Footprint information for reflow soldering

SOT883B

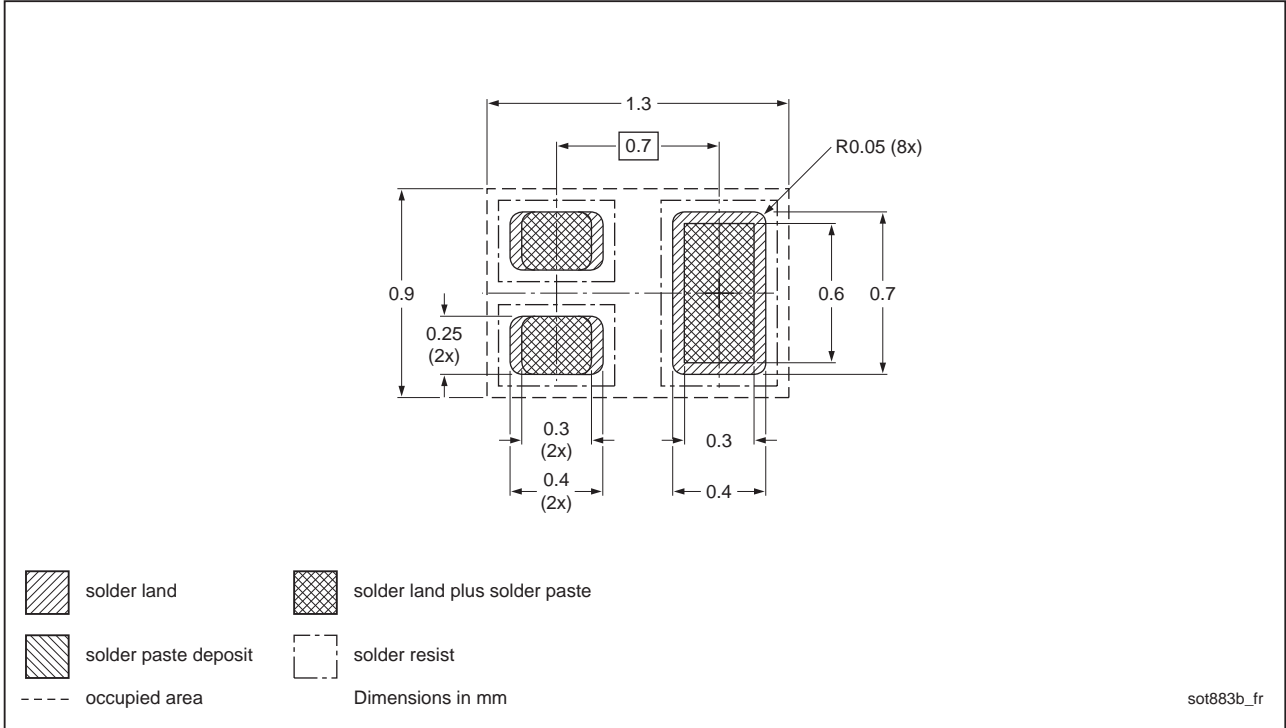


Fig 11. Reflow soldering footprint for SOT883B (DFN1006B-3)

11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTC114YMB v.1	20120516	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1] [2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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